

HIGH VOLTAGE NPN TRANSISTOR

APT27H

General Description

The APT27H series are high voltage, high speed switching NPN power transistor specially designed for off-line switch mode power supplies with low output power.

The APT27H is available in TO-92 package.

Features

- High Switching Speed
- High Collector-Emitter Voltage
- Low Cost

Applications

- Battery Chargers for Mobile Phone
- Power Supply for DVD/STB

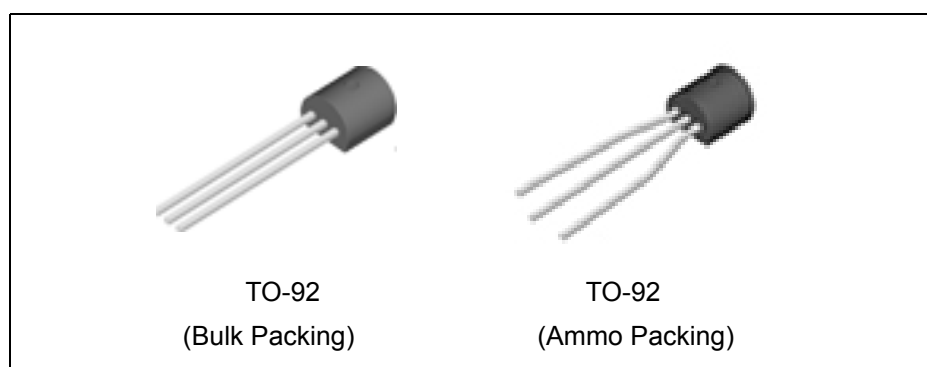


Figure 1. Package Types of APT27H

Pin Configuration

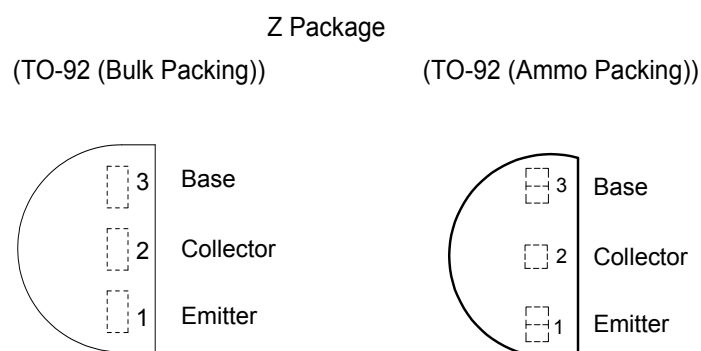
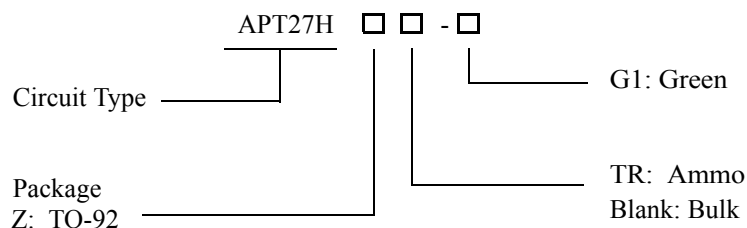


Figure 2. Pin Configuration of APT27H (Top View)

**HIGH VOLTAGE NPN TRANSISTOR****APT27H****Ordering Information**

Package	Part Number	Marking ID	Packing Type
TO-92	APT27HZ-G1	APT27HZ-G1	Bulk
	APT27HZTR-G1	APT27HZ-G1	Ammo

BCD Semiconductor's products, as designated with "G1" suffix in the part number, are RoHS compliant and Green.

Absolute Maximum Ratings (Note 1)

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CES}	800	V
Collector-Emitter Voltage	V_{CEO}	450	V
Emitter-Base Voltage	V_{EBO}	9	V
Collector Current	I_C	0.8	A
Collector Peak Current	I_{CM}	1.6	A
Base Current	I_B	0.4	A
Base Peak Current	I_{BM}	0.8	A
Power Dissipation, $T_A=25^{\circ}\text{C}$	P_{TOT}	0.8	W
Operating Junction Temperature		150	$^{\circ}\text{C}$
Storage Temperature Range		-55 to 150	$^{\circ}\text{C}$

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

**HIGH VOLTAGE NPN TRANSISTOR****APT27H****Thermal Characteristics**

Parameter	Symbol	Value	Unit
Thermal Resistance (Junction to Ambient)	θ_{JA}	156.25	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics($T_C=25^{\circ}\text{C}$, unless otherwise specified.)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector Cut-off Current ($V_{BE}=-1.5\text{V}$)	I_{CEV}	$V_{CE}=800\text{V}$			10	μA
Collector-Emitter Sustaining Voltage ($I_B=0$)	$V_{CEO}(\text{sus})$	$I_C=0.1\text{mA}$	450			V
Collector-Emitter Saturation Voltage	$V_{CE}(\text{sat})$	$I_C=200\text{mA}$, $I_B=40\text{mA}$			0.5	V
DC Current Gain	h_{FE}	$I_C=100\text{mA}$, $V_{CE}=10\text{V}$	15	23	40	
		$I_C=300\text{mA}$, $V_{CE}=10\text{V}$	6	15	30	

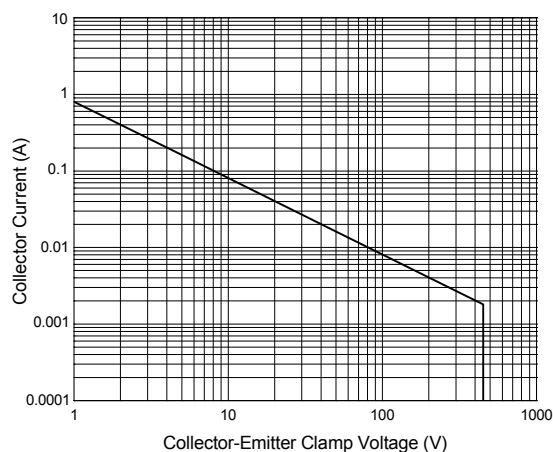
**HIGH VOLTAGE NPN TRANSISTOR****APT27H****Typical Performance Characteristics**

Figure 3. Safe Operating Areas

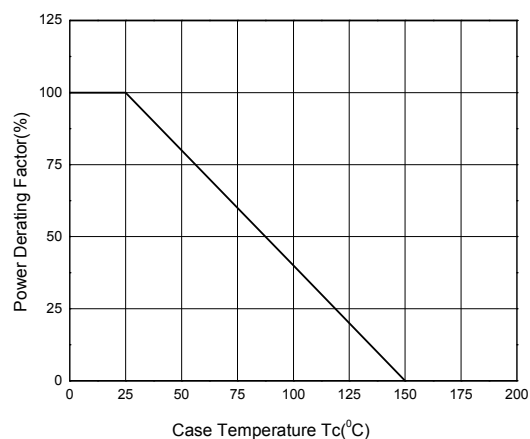


Figure 4. Power Derating Curve

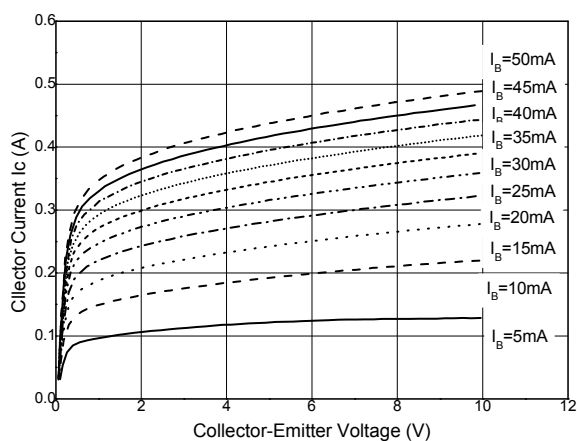


Figure 5. Static Characteristics

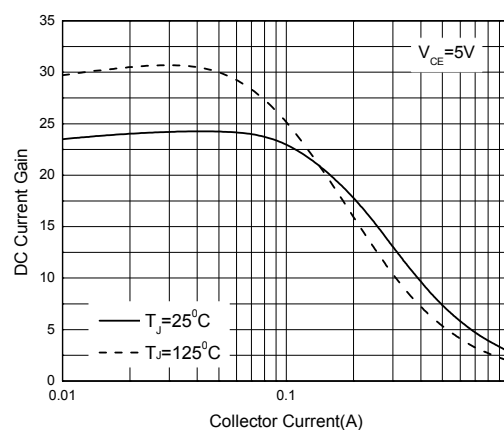


Figure 6. DC Current Gain

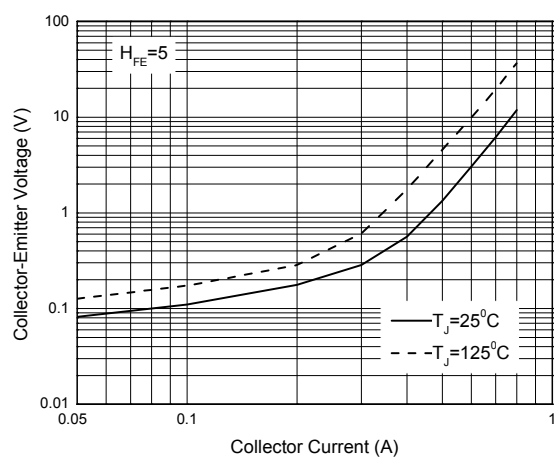
**HIGH VOLTAGE NPN TRANSISTOR****APT27H****Typical Performance Characteristics (Continued)**

Figure 7. Collector-emitter Saturation Region

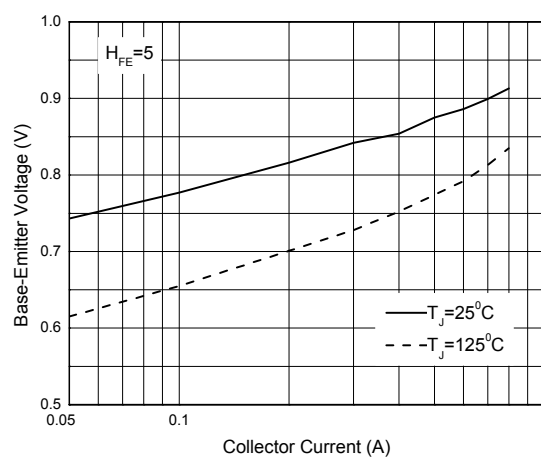
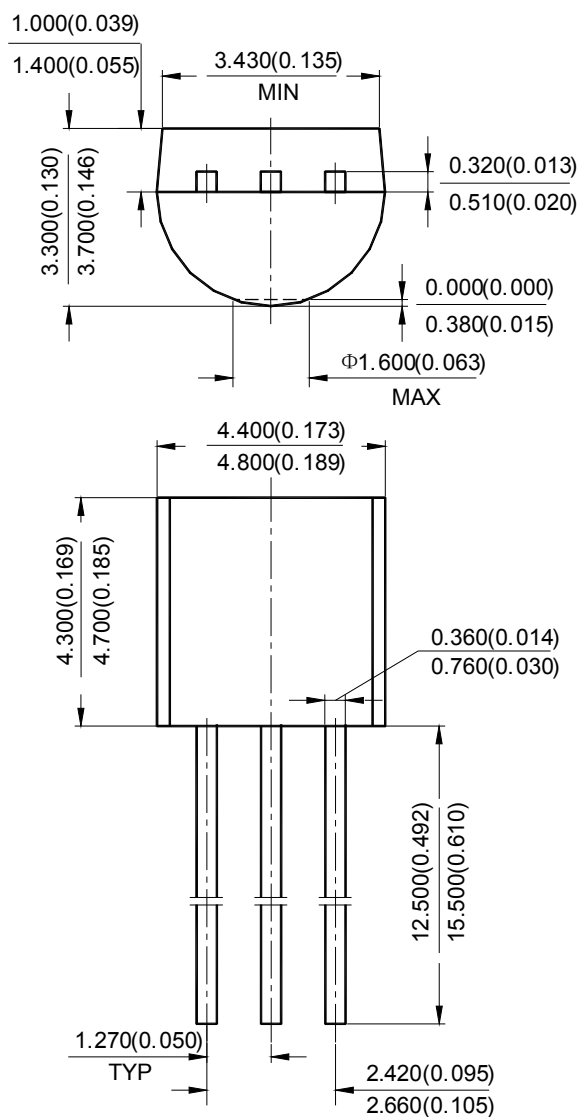


Figure 8. Base-Emitter Saturation Voltage

**HIGH VOLTAGE NPN TRANSISTOR****APT27H****Mechanical Dimensions****TO-92 (Bulk Packing)****Unit: mm(inch)**



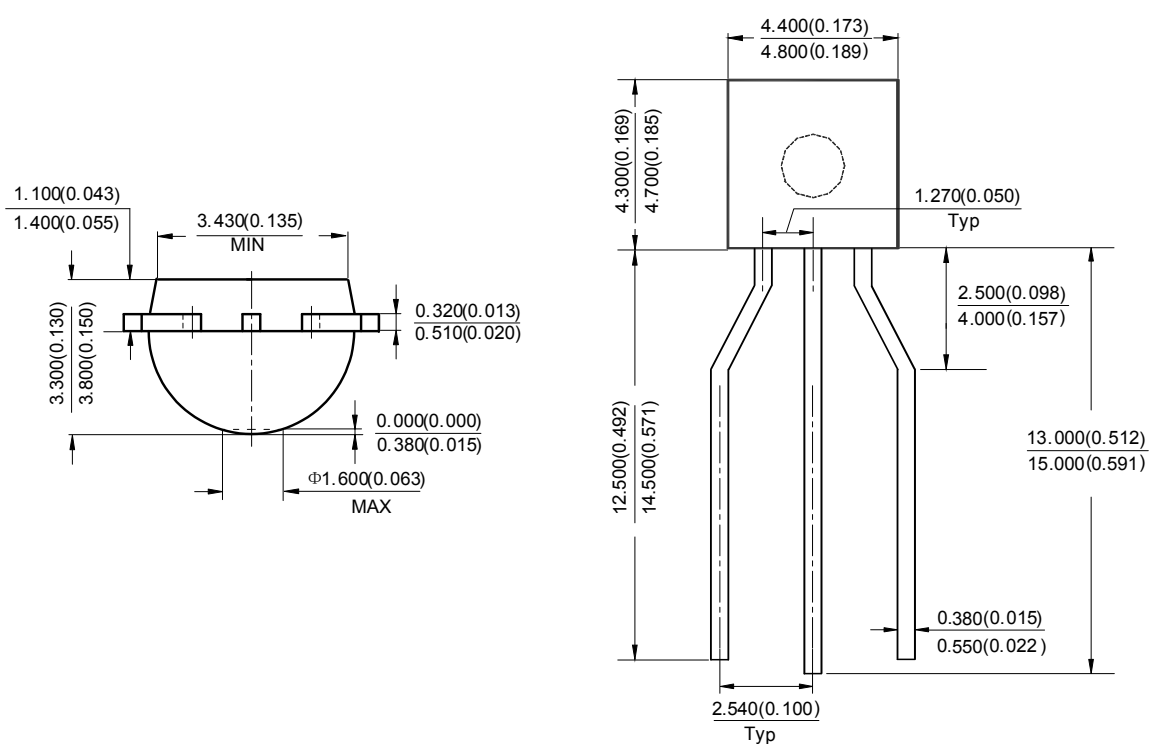
HIGH VOLTAGE NPN TRANSISTOR

APT27H

Mechanical Dimensions (Continued)

TO-92 (Ammo Packing)

Unit: mm(inch)





BCD Semiconductor Manufacturing Limited

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